WNSC6D10650T

Silicon Carbide Diode

Rev.01 - 11 August 2022

Product data sheet

1. General description

Silicon Carbide Schottky diode in a DFN 8*8 plastic package, designed for high frequency switched-mode power supplies.

2. Features and benefits

- New 6th Generation Technology
- Low Forward Voltage Drop
- Low Reverse Leakage Current
- High Forward Surge Capability I_{FSM}
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage				650		V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T _c ≤ 153 °C; <u>Fig. 1; Fig. 2; Fig. 3</u>			10		А
T _j	junction temperature			-55 to 175		°C	
Symbol	Parameter	Conditions	Notes	Min	Min Typ Max		Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 5</u>		-	1.29	1.45	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 5</u>		-	1.45	1.65	V
Dynamic	characteristics					1	
Q _r	recovered charge	I _F = 10 A; dI _F /dt = 500 A/μs; V _R = 400 V; T _j = 25 °C; <u>Fig. 7</u>		-	24	-	nC





5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	n.c.	not connected	[]	к-Ң-А
2	n.c.	not connected	5	001aaa020
3	А	anode		
4	А	anode	8 m m m	
5	К	mounting base; connected to cathode	1 2 3 4	

6. Ordering information

Table 3. Ordering information								
Type number	Package	Orderable part number	Packing	Small packing	Package	Package		
	name		method	quantity	version	issue date		
WNSC6D10650T	DFN8*8	WNSC6D10650T6J	Таре	3000	DFN8X8N	25-Dec-2019		

7. Marking

Table 4. Marking codes						
Type number	Marking codes					
WNSC6D10650T	WNSC6D					
	10650T					

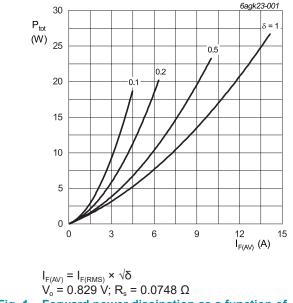
6agk23-002

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{RRM}	repetitive peak reverse voltage			650	V
V_{RWM}	crest working reverse voltage			650	V
V _R	reverse voltage	DC		650	V
I _{F(AV)}	average forward current	δ = 0.5; square-wave pulse; T _c ≤ 153 °C; Fig. 1; Fig. 2; Fig. 3		10	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _c ≤ 153 °C; square-wave pulse		20	A
I _{FSM}	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		75	А
	forward current	$t_p = 10 \ \mu s; T_{j(init)} = 25 \ ^{\circ}C; square-wave pulse$		800	А
l ² t	l ² t for fusing	sine-wave pulse; T _{j(init)} = 25 °C; t _p = 10 ms		28.125	A ² s
T _{stg}	storage temperature			-55 to 175	°C
T _j	junction temperature			-55 to 175	°C



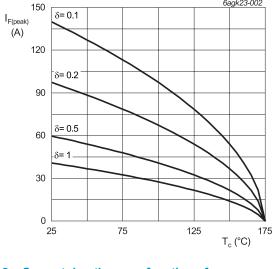
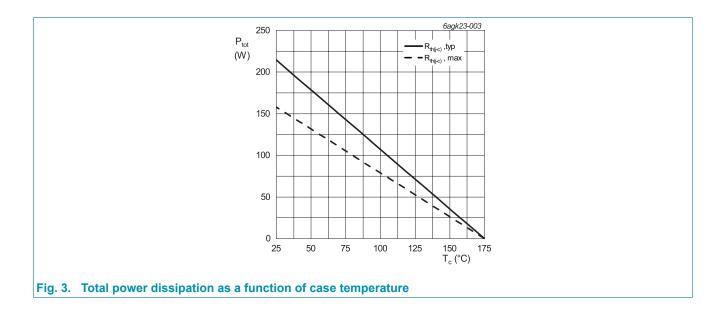




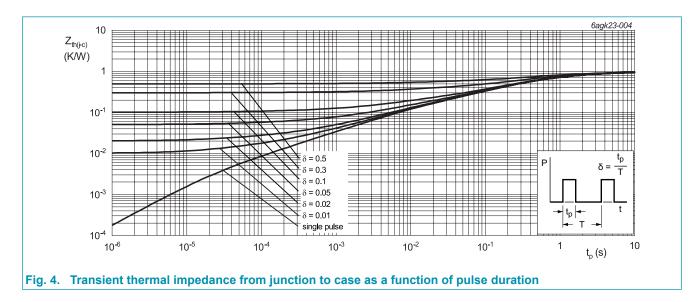
Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

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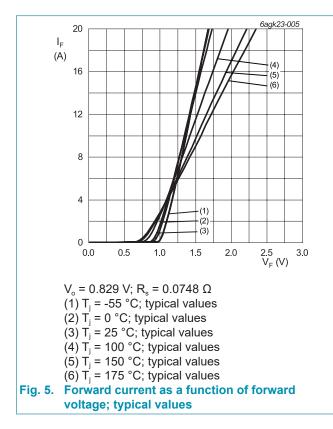
9. Thermal characteristics

Table 6. Th	ermal characteristics						
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	<u>Fig. 4</u>		-	0.7	0.95	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W



10. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static cha	aracteristics						
V _F forward current	forward current	I _F = 10 A; T _j = 25 °C; <u>Fig. 5</u>		-	1.29	1.45	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 5</u>		-	1.45	1.65	V
		I _F = 10 A; T _j = 175 °C; <u>Fig. 5</u>		-	1.50	1.70	V
I _R	reverse current	V _R = 650 V; T _j = 25 °C; <u>Fig. 6</u>		-	1	50	μA
		V _R = 650 V; T _j = 175 °C; <u>Fig. 6</u>		-	15	200	μA
Dynamic	characteristics					_	-
Q _r	recovered charge	$I_F = 10 \text{ A}; V_R = 400 \text{ V}; \text{ d}_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{2}$		-	24	-	nC
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; T _j = 25 °C		-	500	-	pF
		f = 1 MHz; V _R = 300 V; T _j = 25 °C		-	58	-	pF
		f = 1 MHz; V _R = 600 V; T _j = 25 °C		-	52	-	pF
E _{as}	non-repetitive avalanche energy	I _R = 5 A; L = 5 mH; T _{j(init)} = 25 °C		60	-	-	mJ



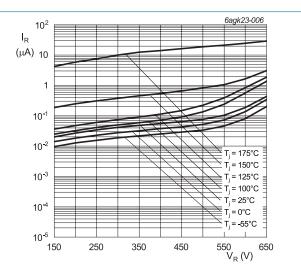
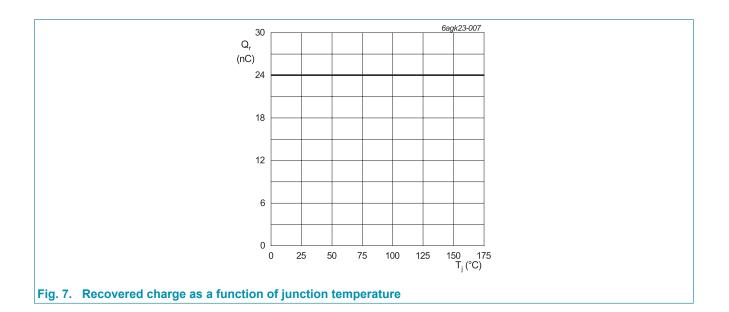
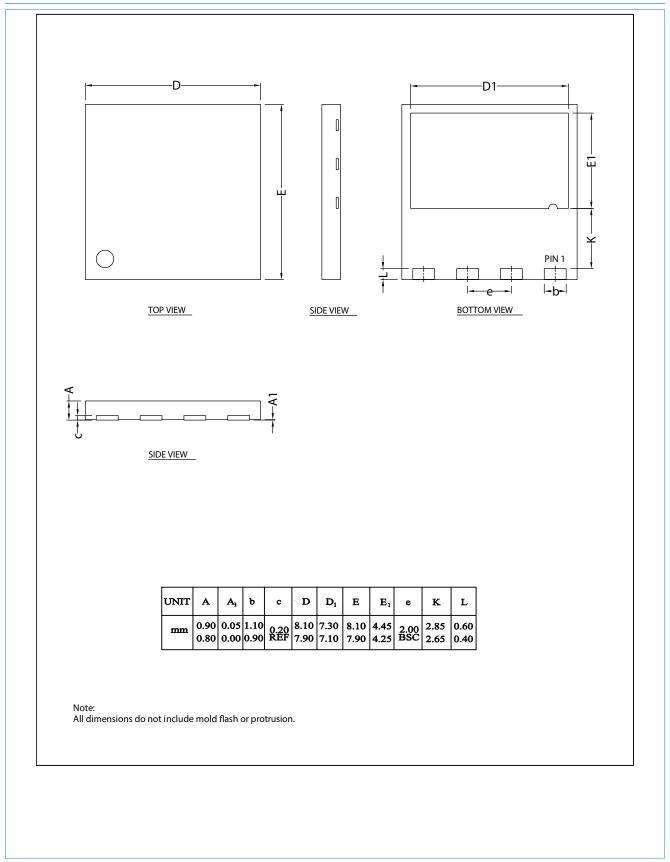


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value

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11. Package outline



WNSC6D10650T Product data sheet

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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
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